Computational Investigations of the Bulk and Surface Properties of CaSnS₃ Sami Al Azri; Henry I. Eya; Nelson Y. Dzade John and Willie Leone Family Department of Energy and Mineral Engineering, Penn State

INTRODUCTION

In recent years, the demand for sustainable energy sources increased rapidly in efforts to decarbonize various sectors.^[1] Photovoltaic conversion has long been on the horizon as the most compelling technological option for producing 'green' energy from widely available sunlight. Harnessing this energy and designing our infrastructure around it will mitigate the adverse environmental and societal consequences of climate change.



Hybrid organic-inorganic lead halide perovskites (HOIPs) have attracted significant attention recently as one of the most promising photovoltaic technologies owing to their high efficiency, low-cost, solution-processibility, and exceptional optoelectronic properties.^{[4][5]}

The record PCE of halide perovskites (over 25% in singlejunction cells and over 29% in tandem cells with silicon) shows a great promise.^[6]

However, the toxicity of the lead content and the intrinsic instability of lead-halide perovskites materials have remained significant challenges to their large-scale applications and commercialization.

CHALCOGENIDE PEROVSKITES

- Chalcogenide perovskites have recently emerged promising alternatives to HOIPs owing to their remarkable chemical and thermal stability up to 600 degrees Celsius and under-water immersion.^[7]
- The are characterized by record-high dielectric polarizability, while also featuring tunable bandgap (E_g) in the visible and near infrared region of the solar spectrum (1.4–2.1 eV).^[8]
- \Box Possess high absorption coefficients near the band edge ($\sim 10^5$ cm⁻¹ in contrast to 10^4 cm⁻¹ for CdTe and Si).^[9]
- **PV** device simulation shows that 38% efficiency can be reached in a chalcogenide perovskite/crystalline Si tandem architecture.^[10]
- \Box They have huge compositional degrees of freedom (ABX₃), where A and B are metals with a combined valence of 6 and X stand for S or Se). Examples: BaZrS₃, BaZrSe₃, SrZrS₃, CaZrSe₃, **CaSnS₃**, etc.



RESEARCH OBJECTIVES

The nature of the surface of the absorber material (i.e., the composition and stability) dictates its interfacial structures with charge transport layers.



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metal top contact interlayer electron transport layer

metal halide perovskite

hole transport layer transparent electrode glass

- > Determine the structural parameters of **CaSnS**₃
- Accurately predict the bandgap and electronic structures (band structure and density of states) of CaSnS₃.
- Predict the optical properties (absorption) coefficient, dielectric reflectivity, CaSnS₃.
- > Characterize the surface structures, composition and relative stabilities of the different Miller-index surfaces of CaSnS₃.
- \succ Determine the electronic properties (i.e., the work function, ionization potential, and electron affinity) of the different surfaces of CaSns₃.

STRUCTURAL AND ELECTRONIC PROPERTIES OF BULK CASNS3

constant, refractive index, etc.) of

CaSnS₃ **Crystallizes** in the **orthorhombic phase**

Space group: Pnma

Lattice	DFT-D3
parameter	
a (Å)	6.647
b (Å)	7.033
c (Å)	9.580



SURFACE COMPOSITION AND STABILITY ANALYSIS

The surface stability trend is predicted to be: (010) < (100) < (011) < (111) < (001) < (110)

Surfaces Energies [γ(Jm ⁻²)]	
(001)	0.5983
(010)	0.4527
(100)	0.5257
(011)	0.5456
(101)	0.6613
(110)	0.6415
(111)	0.5642

$CaSnS_{3}(010)$

METHODOLOGY & COMPUTATIONAL DETAILS





In summary, we have characterized the bulks and surface properties of CaSnS₃ using first-principles DFT methodology with Grimme's dispersion correction and Hybrid HSE06 functional.

- energy of 0.45 Jm-2.

Ongoing and future calculations will systematically characterize optical properties of the bulk CaSnS₃ We will also characterize the electronic properties (work function, ionization) potential, and electron affinity) of the different surfaces of CaSnS₃

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CONCLUSIONS

The orthorhombic structural parameters are predicted in good agreement with experiment

The Electronic bandgap is predicted at 1.76 eV, which is consistent UV-vis measurement

Source band edge of CaSnS3 is dominated by S-p states whereas the conduction band edge has major contribution from both the S-p an Sn-s states

 \checkmark The most stable surface of CaSnS3 is predicted to be the (010) surface with a surface

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